

MOS FIELD EFFECT TRANSISTOR NP82P04PLF

SWITCHING P-CHANNEL POWER MOSFET

DESCRIPTION

The NP82P04PLF is P-channel MOS Field Effect Transistor designed for high current switching applications.

<R> ORDERING INFORMATION

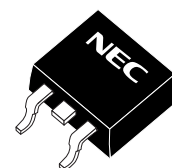
PART NUMBER	LEAD PLATING	PACKING	PACKAGE
NP82P04PLF-E1-AY ^{Note}	Pure Sn (Tin)	Tape 800 p/reel	TO-263 (MP-25ZP)
NP82P04PLF-E2-AY ^{Note}			

Note Pb-free (This product does not contain Pb in external electrode.)

FEATURES

- Super low on-state resistance
 $R_{DS(on)1} = 8 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -41 \text{ A)}$
 $R_{DS(on)2} = 12 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -41 \text{ A)}$
- Low input capacitance
 $C_{iss} = 5000 \text{ pF TYP.}$
- Built-in gate protection diode

(TO-263)



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-40	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±82	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±246	A
Total Power Dissipation (T _C = 25°C)	P _{T1}	150	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.8	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to +175	°C
Repetitive Avalanche Current ^{Note2}	I _{AR}	46	A
Repetitive Avalanche Energy ^{Note2}	E _{AR}	212	mJ

Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. T_{ch} ≤ 150°C, V_{DD} = -20 V, R_G = 25 Ω, V_{GS} = -20 → 0 V

THERMAL RESISTANCE

Channel to Case Thermal Resistance	R _{th(ch-C)}	1.0	°C/W
Channel to Ambient Thermal Resistance	R _{th(ch-A)}	83.3	°C/W

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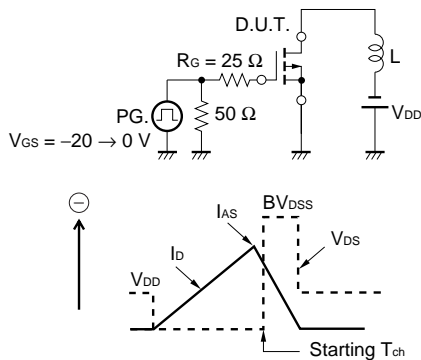
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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

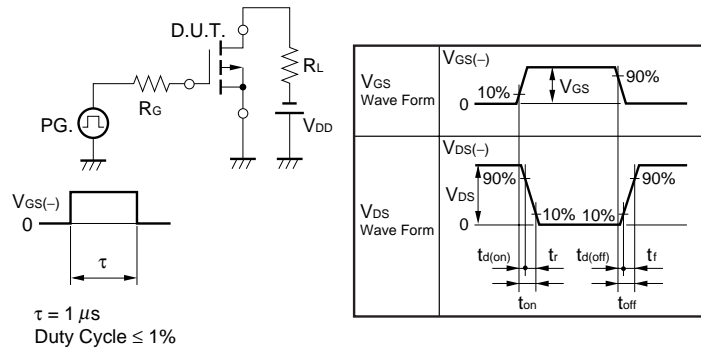
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -40 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = -10 V, I _D = -1 mA	-1.5	-2.0	-2.5	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = -10 V, I _D = -41 A	28	58		S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}	V _{GS} = -10 V, I _D = -41 A		6.5	8	mΩ
	R _{DS(on)2}	V _{GS} = -4.5 V, I _D = -41 A		8.3	12	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V,		5000		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V,		1100		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		440		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -20 V, I _D = -41 A,		17		ns
Rise Time	t _r	V _{GS} = -10 V,		18		ns
Turn-off Delay Time	t _{d(off)}	R _G = 0 Ω		126		ns
Fall Time	t _f			58		ns
Total Gate Charge	Q _G	V _{DD} = -32 V,		90		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -10 V,		15		nC
Gate to Drain Charge	Q _{GD}	I _D = -82 A		21		nC
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = -82 A, V _{GS} = 0 V		0.96	1.5	V
Reverse Recovery Time	t _{rr}	I _F = -82 A, V _{GS} = 0 V,		48		ns
Reverse Recovery Charge	Q _{rr}	di/dt = -100 A/μs		62		nC

Note Pulsed test PW ≤ 350 μs, Duty Cycle ≤ 2%

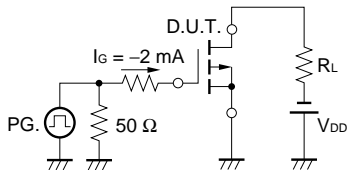
TEST CIRCUIT 1 AVALANCHE CAPABILITY



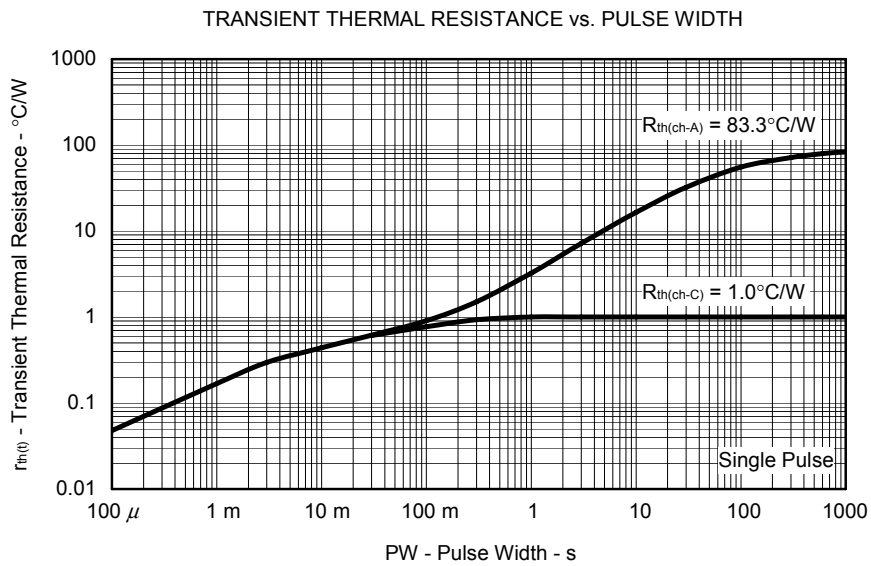
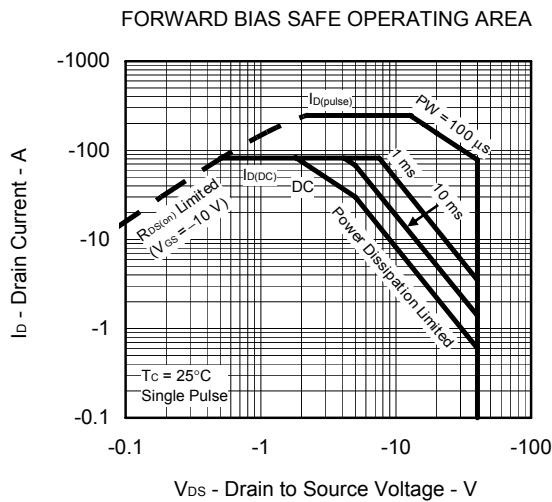
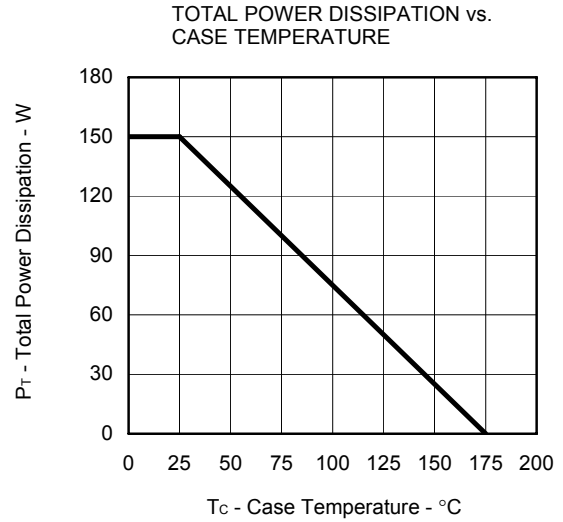
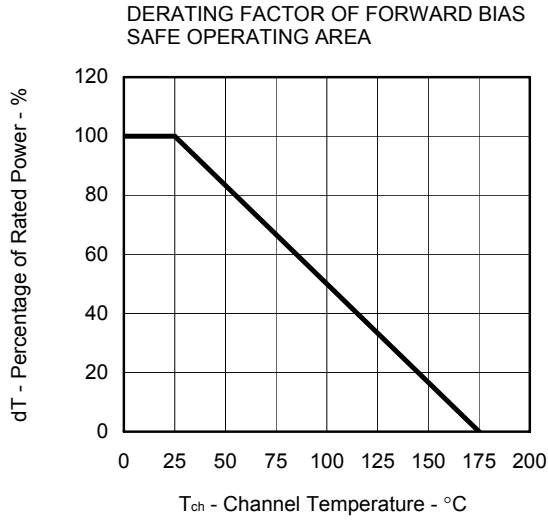
TEST CIRCUIT 2 SWITCHING TIME



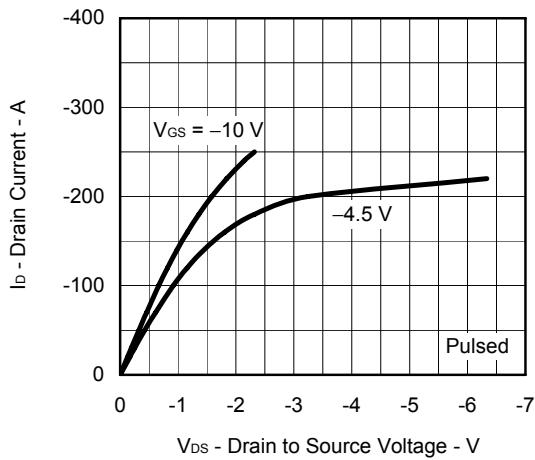
TEST CIRCUIT 3 GATE CHARGE



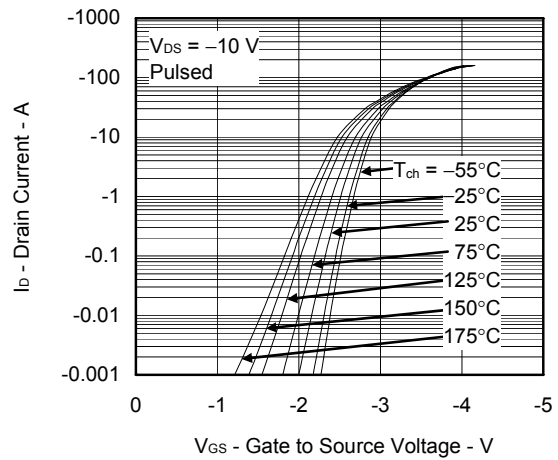
TYPICAL CHARACTERISTICS (T_A = 25°C)



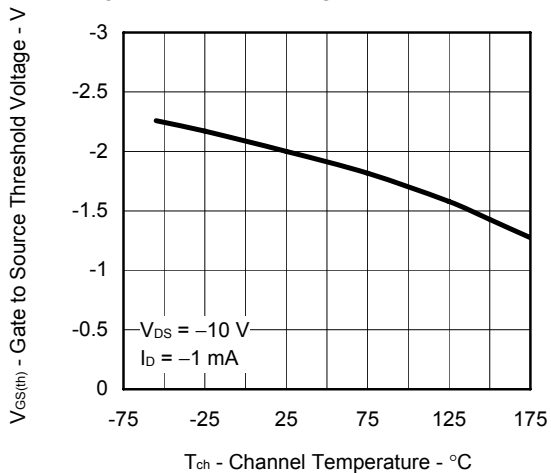
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



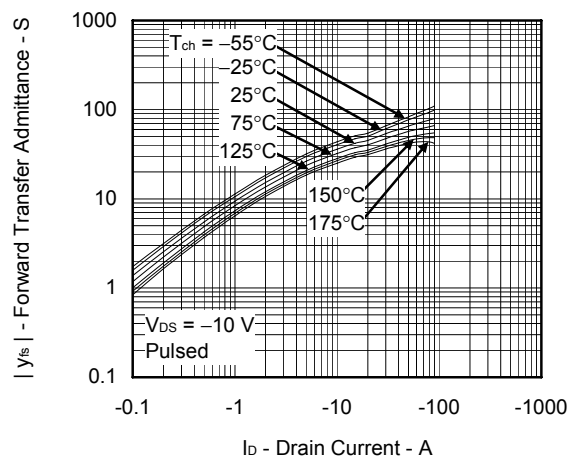
FORWARD TRANSFER CHARACTERISTICS



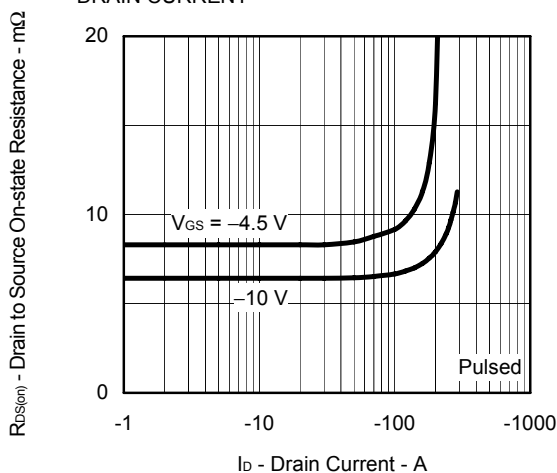
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



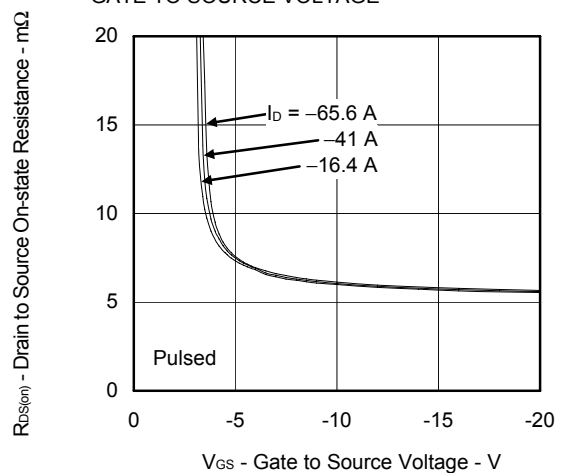
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



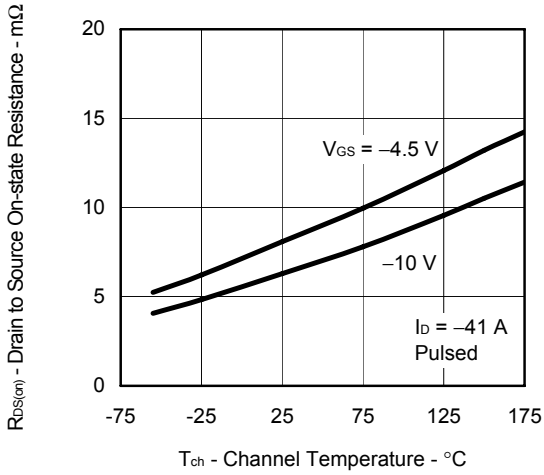
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



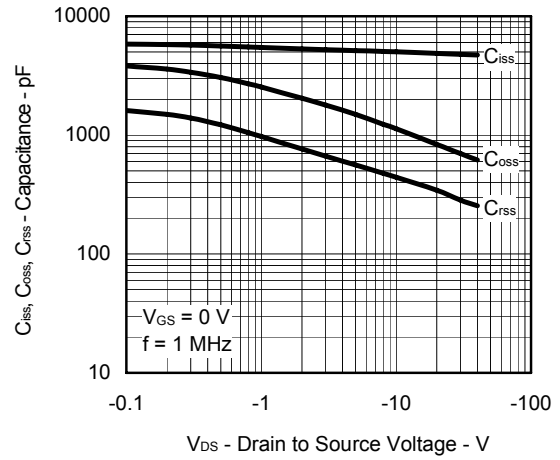
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



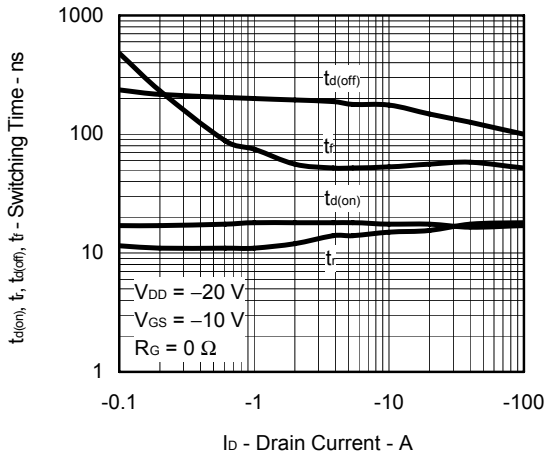
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



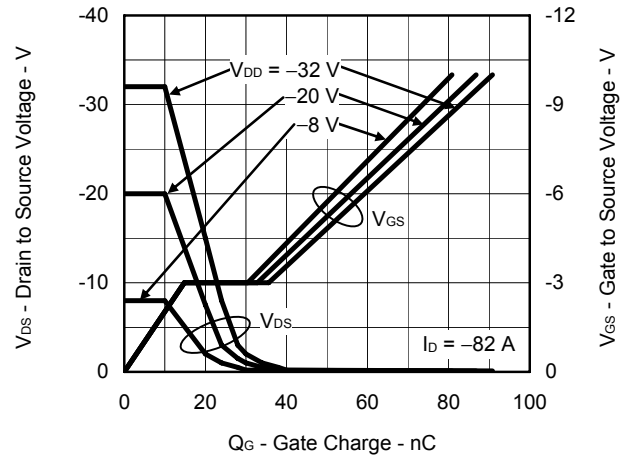
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



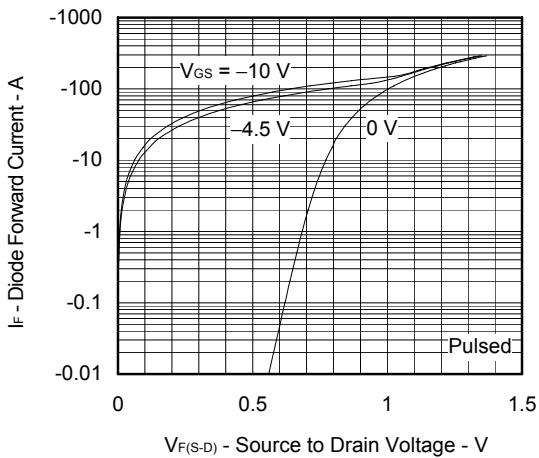
SWITCHING CHARACTERISTICS



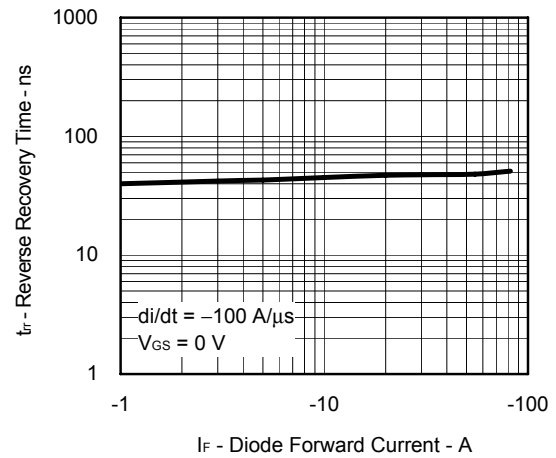
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

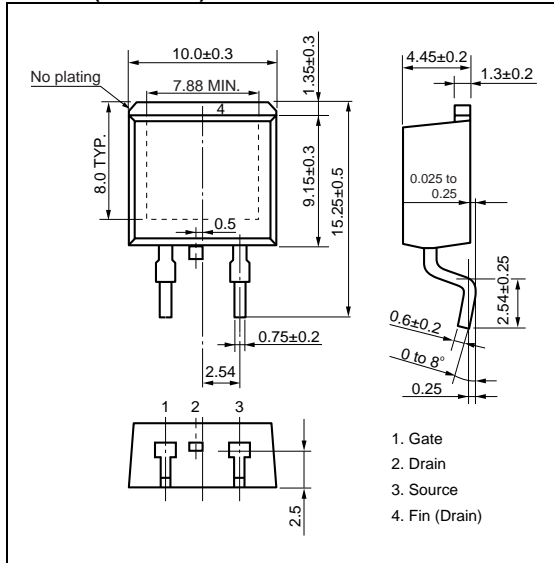


REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

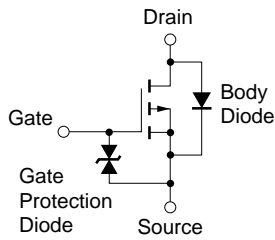


PACKAGE DRAWING (Unit: mm)

TO-263 (MP-25ZP)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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